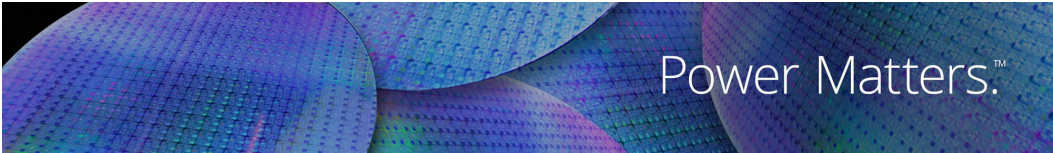


POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Silicon Carbide (SiC) Semiconductor
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
 - BJT Modules (Power Integrated Circuit, PIC)
 - Darlington Transistors
 - Darlington Transistor Array
 - NPN PNP Complimentary Transistor
 - NPN Transistor
 - **PNP Transistor**
- ▶ Legacy Power Discretes & Modules
- ▶ Diode and Rectifier Devices



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2N5147 (#23773)

Product Status

In Production

Overview

Resources

Diagrams

Ordering

Support

Package ESD Bag
Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.46	V
DC Current Gain	HFE	30		90	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter O	V _{BR(CBO)}			100	V
Collector Current (dc)	I _C			-2	A
Collector-Emitter Voltage (Base Open)	V _{CEO}			80	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			5.5	V
Power Dissipation	P _D			7	W

Alphanumeric Parameter	Value
Quality Level	-

This part can be found in the following product categories:

- Power Discretes & Modules ▶ BJT (BiPolar Junction Transistor)
- Power Discretes & Modules ▶ BJT (BiPolar Junction Transistor) ▶ PNP Transistor